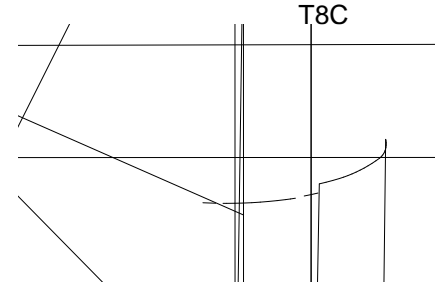


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Device Type	$V_{RRM}$ (1)	$V_{DRM}$ (1)	$V_{RSM}$ (1)
KP1150/40	4000	4000	4100
KP1150/42	4200	4200	4300
KP1150/45	4500	4500	4600

$V_{RRM}$  = Repetitive peak reverse voltage  
 $V_{DRM}$  = Repetitive peak off state voltage  
 $V_{RSM}$  = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	$I_{RRM}/I_{DRM}$	5 mA 100 mA (3)
Critical rate of voltage rise	dv/dt (4)	1000 V/ s

Peak gate power dissipation	$P_{GM}$	20	W	
Average gate power dissipation	$P_{G(AV)}$	4	W	
Gate-trigger current	$I_{GT}$	200	mA	$V_D = 12\text{ V}; R_L = 3\text{ ohms}; T_j = +25\text{ }^\circ\text{C}$
Gate-trigger voltage	$V_{GT}$	0.7	2.6	V $V_D = 12\text{ V}; R_L$

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